

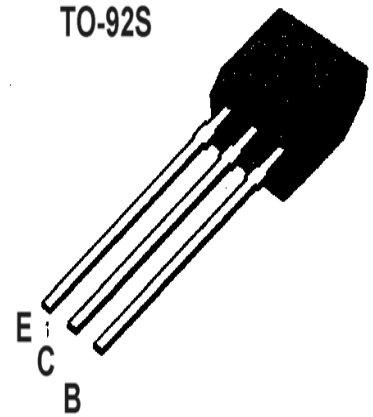
PNP Transistors

—PNP Silicon—

■■ APPLICATION: Low Frequency Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-20	V
Collector-emitter voltage	V _{CEO}	-20	V
Emitter-base voltage	V _{EB0}	-6	V
Collector current	I _c	-2	A
Collector current (Pluse)	I _{cp}	-5	A
Collector Power Dissipation	P _c	0.4	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C, R_G=10Ω)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Emitter Breakdown Voltage	BV _{cbo}	-20			V	I _c =-50uA	I _e =0	
Collector-Emitter Saturation Voltage	BV _{ceo}	-20			V	I _c =-1mA	I _b =0	
Base-Emitter Saturation Voltage	BV _{ebo}	-6			V	I _e =-50uA	I _c =0	
Collector Cut-off Current	I _{cbo}			-0.1	uA	V _{cb} =-20V	I _e =0	
Emitter Cut-off Current	I _{ebo}			-0.1	uA	V _{eb} =-5V	I _c =0	
Collector-Emitter Saturation Voltage	V _{ce(sat)}			-0.5	V	I _c =-2A	I _b =-0.1A	
DC Current Gain	h _{FE}	120		390	β	V _{ce} =-2V	I _c =-0.1A	
Gain bandwidth product	f _T		240		MHz	V _{ce} =-2V	I _e =0.5A	f=100MHz
Common Base Output Capacitance	C _{ob}		35		pF	V _{cb} =-10V	I _e =0	f=1MHz

■■ h_{FE} Classification And Marking

Mark	A1585S	
Classification	Q	R
h _{FE}	120~270	180~390